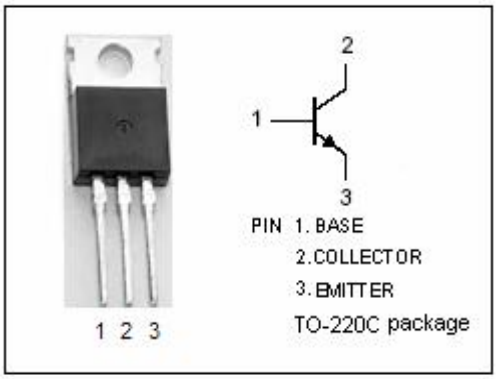
isc Silicon NPN Power Transistor — BD637



DESCRIPTION

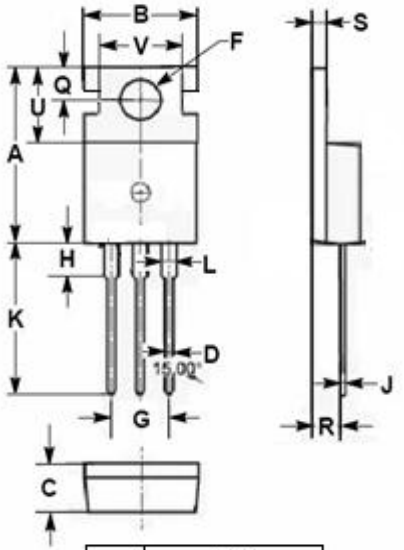
- DC Current Gain -
  : h_{FE} = 40(Min.)@ I_C= 25mA
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V(Min.)
- Complement to Type BD638
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
I_{CM}	Collector Current-Peak	5	A
I_B	Base Current-Continuous	0.3	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA; I_B= 0	80		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 0.1mA; I_E= 0	100		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A		0.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 1A; V_{CE}= 2V		1.3	V
I_{CES}	Collector Cutoff Current	V_{CE}= 100V; V_{BE}= 0		0.2	mA
h_{FE-1}	DC Current Gain	I_C= 25mA; V_{CE}= 2V	40		
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 2V	25		